

# NCE15G135P

## 1350V, 15A, Trench NPT IGBT

## **Features**

- Trench NPT( Non Punch Through) IGBT
- High speed switching
- Low saturation voltage: V<sub>CE(sat)</sub>=2.0V@I<sub>C</sub>=15A
- High input impedance

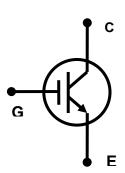
# GCE

## **Applications**

- Inductive heating, Microwave oven, Inverter, UPS, etc.
- Soft switching applications



Using advanced Trench NPT technology, NCE's 1350V IGBTs offers superior conduction and switching performances, and easy parallel operation with exceptional avalanche ruggedness. This device is designed for soft switching applications.



# **Absolute Maximum Ratings**

Symbol	Description	Ratings	Units
V <sub>CES</sub>	Collector to Emitter Voltage	1350	V
$V_{GES}$	Gate to Emitter Voltage	+/-30	V
I <sub>C</sub>	Continuous Collector Current @T <sub>C</sub> =25°C	30	Α
	Continuous Collector Current @T <sub>C</sub> =100°C	15	Α
I <sub>CM</sub> (1)	Pulsed Collector Current	45	Α
$P_D$	Maximum Power Dissipation @T <sub>C</sub> =25°C	220	W
	Maximum Power Dissipation @T <sub>C</sub> =100°C	88	W
TJ	Operating Junction Temperature	-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5seconds	300	°C

#### Notes:

1. Repetitive rating, Pulse width limited by max. junction temperature



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## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
R <sub>JC</sub>	Thermal Resistance, Junction to Case	-	0.57	°C/W
$R_{JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

# Electrical Characteristics of the IGBT T<sub>C=25°C</sub>

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Characteristics						
$BV_CES$	Collector to Emitter		1350	_	_	V
	Breakdown Voltage	V <sub>GE</sub> =0V, Ic=1mA	1330	_	_	V
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0V$	-	-	1	mA
$I_{GES}$	G-E Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0V$	-	-	+/-250	nA
On Char	acteristics					
$V_{\text{GE(th)}}$	G-E Threshold Voltage	I <sub>C</sub> =15mA, V <sub>CE</sub> =V <sub>GE</sub>	4.0	5.5	7.0	V
	Collector to Emitter Coturation	I <sub>C</sub> =15A, V <sub>GE</sub> =15V	-	2	2.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$T_{C}$ =25°C $I_{C}$ =15A, $V_{GE}$ =15V $T_{C}$ =125°C	-	2.15	-	V
Dynamic	Characteristics					
C <sub>ies</sub>	Input Capacitance		-	2350	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE}$ =30V, $V_{GE}$ =0V,	-	70	-	pF
C	Reverse Transfer	f=1MHz	45		nE	
$C_{res}$	Capacitance		-	40	-	pF
Switchin	g Characteristics					
$t_{d(on)}$	Turn-On Delay Time		-	33	-	ns
t <sub>r</sub>	Rise Time	\/ -600\/  -154	-	80	-	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time	$V_{CC}$ =600V, $I_{C}$ =15A, $R_{G}$ =10 $\Omega$ , $V_{GE}$ =15V,	-	160	-	ns
$t_f$	Fall Time	Resistive Load,	-	255	330	ns
$E_{on}$	Turn-On Switching Loss	T <sub>C</sub> =25°C	-	0.3	-	mJ
$E_{off}$	Turn-Off Switching Loss	10-25 0	-	0.58	0.74	mJ
E <sub>ts</sub>	Total Switching Loss		-	0.88	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	30	-	ns
t <sub>r</sub>	Rise Time	\/ -600\/   -154	-	115	-	ns
$t_{d(off)}$	Turn-Off Delay Time	V <sub>CC</sub> =600V,I <sub>C</sub> =15A,	-	170	-	ns
$t_f$	Fall Time	$R_G$ =10Ω, $V_{GE}$ =15V, Resistive Load, $T_C$ =125°C	-	390	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	0.38	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss	10-123 C	-	0.89	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	1.27	-	mJ
$Q_g$	Total Gate Charge	\/=600\/	_	100	-	nC
$Q_{ge}$	Gate to Emitter Charge	$V_{CC}$ =600V, $I_{C}$ =15A, $V_{GE}$ =15V	-	19	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	V GE-13V	-	45	-	nC

## **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 

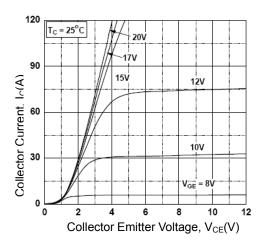


Figure 3. Saturation Voltage vs. Case

Temperature at Variant Current Level

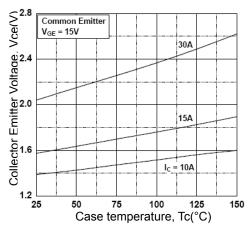


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

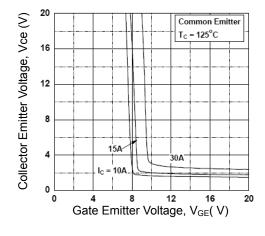


Figure 2. Typical Saturation Voltage Characteristics

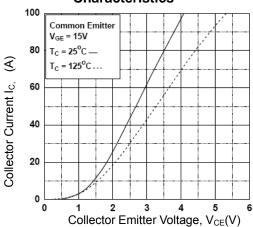


Figure 4. Saturation Voltage vs.  $V_{\text{GE}}$ 

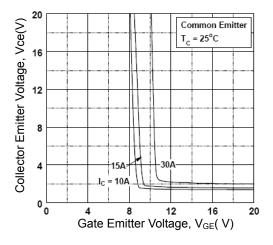
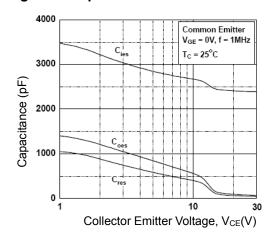


Figure 6. Capacitance Characteristics





## **Typical Performance Characteristics (Continued)**

Figure 7. Turn-on Characteristics vs. Gate Resistance

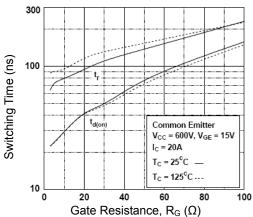


Figure 9. Switching Loss vs. Gate Resistance

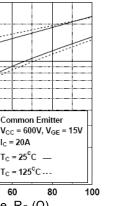


Figure 10. Turn-on Characteristics vs. Collector

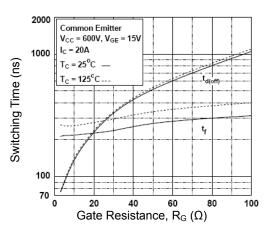
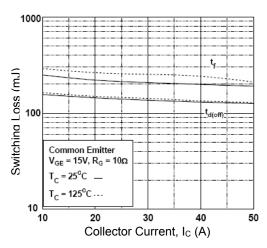


Figure 8. Turn-off Characteristics vs. Gate

Resistance

Common Emitter  $V_{CC} = 600V, V_{GE} = 15V$ I<sub>C</sub> = 20A T<sub>C</sub> = 25°C Switching Loss (mJ) = 125°C ---40 60 100 Gate Resistance, R<sub>G</sub> (Ω)

Figure 11. Turn-Off Characteristics vs. **Collector Current** 



Current

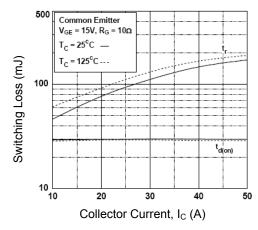
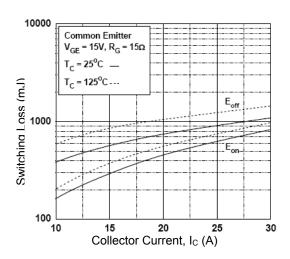


Figure 12. Switching Loss vs. Collector Current





## **Typical Performance Characteristics (Continued)**

### Figure 13. Gate Charge Characteristics

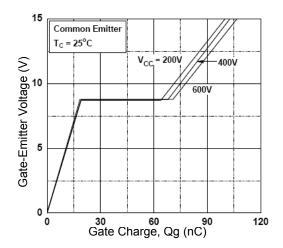


Figure 15. Turn-Off SOA

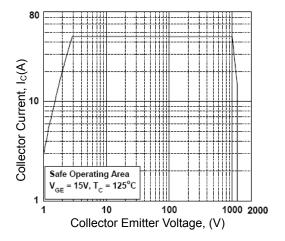


Figure 14. SOA Characteristics

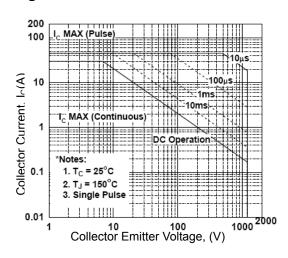
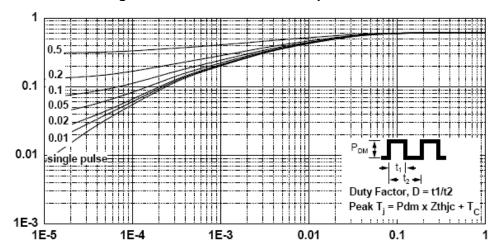
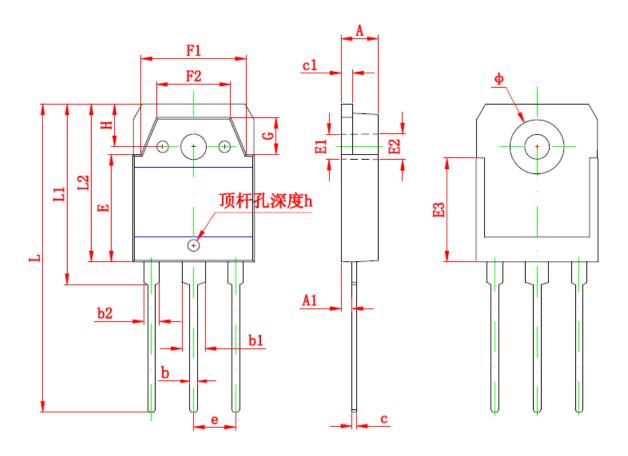


Figure 16. Transient Thermal Impedance of IGBT





# **TO-3P Mechanical Dimensions**



Sumbal	Dim ensions In Millim eters		Dimensions In Inches			
Symbol	Min	Max	Min	Max		
Α	4.600	5.000	0.181	0.197		
A 1	1.200	1.600	0.047	0.063		
b	0.800	1.200	0.031	0.047		
b1	2.800	3.200	0.110	0.126		
b2	1.800	2.200	0.071	0.087		
С	0.500	0.700	0.020	0.028		
c 1	1.450	1.650	0.057	0.065		
D	15.450	15.850	0.606	0.622		
Е	13.700	14.100	0.539	0.555		
E 1	3.200	REF	0.126	REF		
E 2	3.300	3.300 REF		0.130 REF		
E 3	13.45	13.450 REF		0.530 REF		
F 1	13.400	13.800	0.528	0.543		
F 2	9.400	9.800	0.370	0.386		
L	39.900	40.300	1.571	1.587		
L 1	23.200	23.600	0.913	0.929		
L2	20.300	20.600	0.799	0.811		
Φ	6.900	7.100	0.272	0.280		
G	5.150	5.550	0.203	0.219		
е	5.450	TYP	0.21	5 TYP		
Н	5.000	REF	0.197	7 REF		
h	0.000	0.300	0.000	0.012		



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